MOSFETs Silicon N-channel MOS (U-MOSⅧ)

# TPN2R503NC

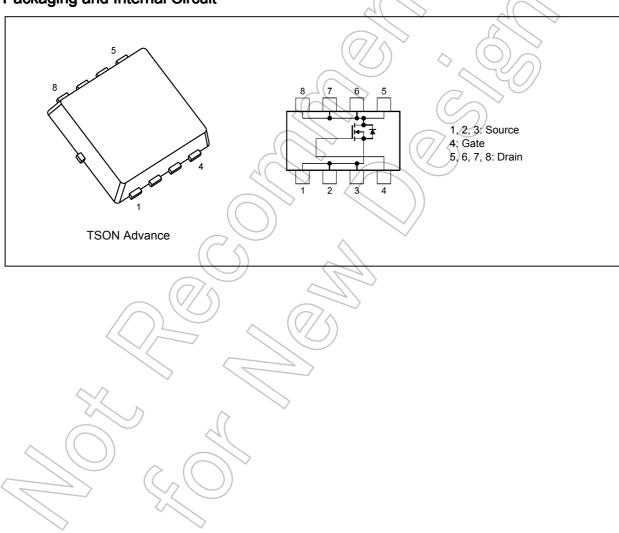
#### 1. Applications

Power Management Switches

#### 2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 2.1 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (3) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- (4) Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V (V\_{DS} = 10 V,  $I_{D}$  = 0.5 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteris	tics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	30	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	ID C	85	А
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	40	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I <sub>DP</sub>	120	
Power dissipation	(T <sub>c</sub> = 25°C)		PD	35	W
Power dissipation	(t = 10 s)	(Note 3)	Pp	1.9	W
Power dissipation	(t = 10 s)	(Note 4)	PD	0.7	W
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	62	mJ
Avalanche current				40	А
Channel temperature		6	T <sub>ch</sub>	150	°C
Storage temperature		21	Tstg	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

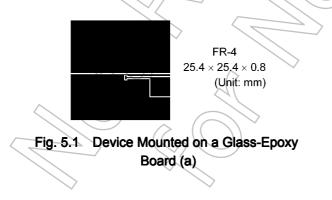
#### 5. Thermal Characteristics

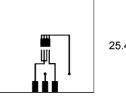
Characteristics			Symbol	Max	Unit
Channel-to-case thermal resistance	(T <sub>c</sub> = 25°C)	$\langle \rangle$	R <sub>th(ch-c)</sub>	3.57	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	65.7	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R <sub>th(ch-a)</sub>	178	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

- Note 2: Limited by silicon capability, Package limit is 45 A.
- Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1
- Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD}$  = 24 V,  $T_{ch}$  = 25°C (initial), L = 30  $\mu$ H, R<sub>G</sub> = 1  $\Omega$ , I<sub>AR</sub> = 40 A





FR-4 25.4 × 25.4 × 0.8 (Unit: mm)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

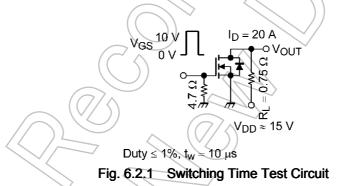
## 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_		±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	Y	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30		—	V
Drain-source breakdown voltage (Note 6)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	15	)~	—	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 mA	1.3	2_	2.3	
Drain-source on-resistance	R <sub>DS(ON)</sub>	$V_{GS}$ = 4.5 V, I <sub>D</sub> = 20 A	$/ \uparrow$	3.2	4.1	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	$\sum$	2.1	2.5	

Note 6: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

## 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz$		2230	) —	pF
Reverse transfer capacitance	C <sub>rss</sub>		$\mathcal{A}$	160		
Output capacitance	C <sub>oss</sub>		$\sim$	650		
Switching time (rise time)	tr	See Figure 6.2.1.	$\sim )$	9	_	ns
Switching time (turn-on time)	t <sub>on</sub>		$\sim$	14		
Switching time (fall time)	t <sub>f</sub>		))_	24	_	
Switching time (turn-off time)	t <sub>off</sub>		_	68	_	



## 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

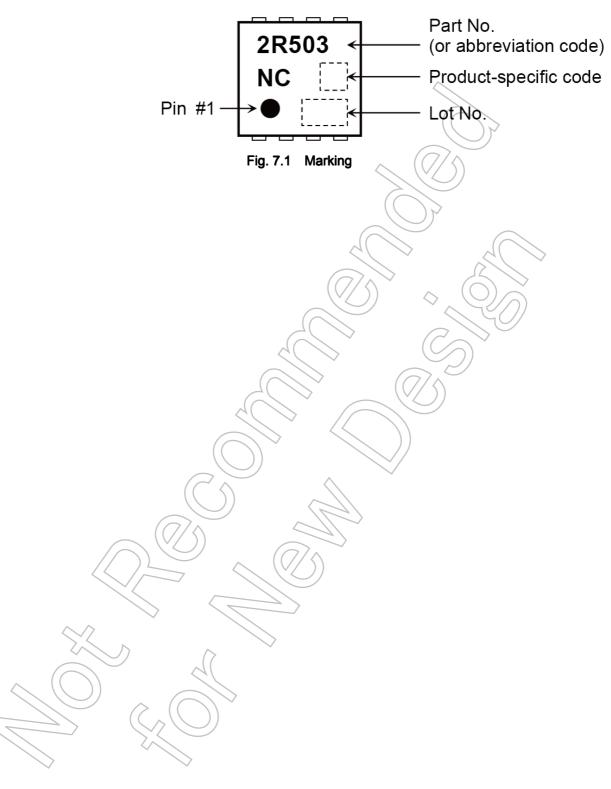
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD}\approx 24~V,~V_{GS}$ = 10 V, I <sub>D</sub> = 40 A	_	40	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	10	—	
Gate-drain charge	Q <sub>gd</sub>			10		

## 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

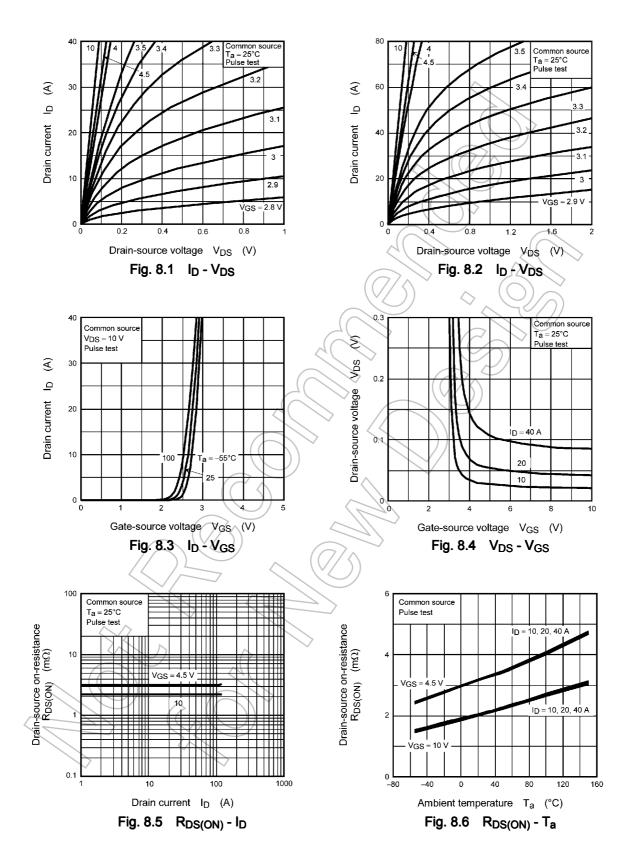
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 7)	I <sub>DRP</sub>	—	_	—	120	А
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 40 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V

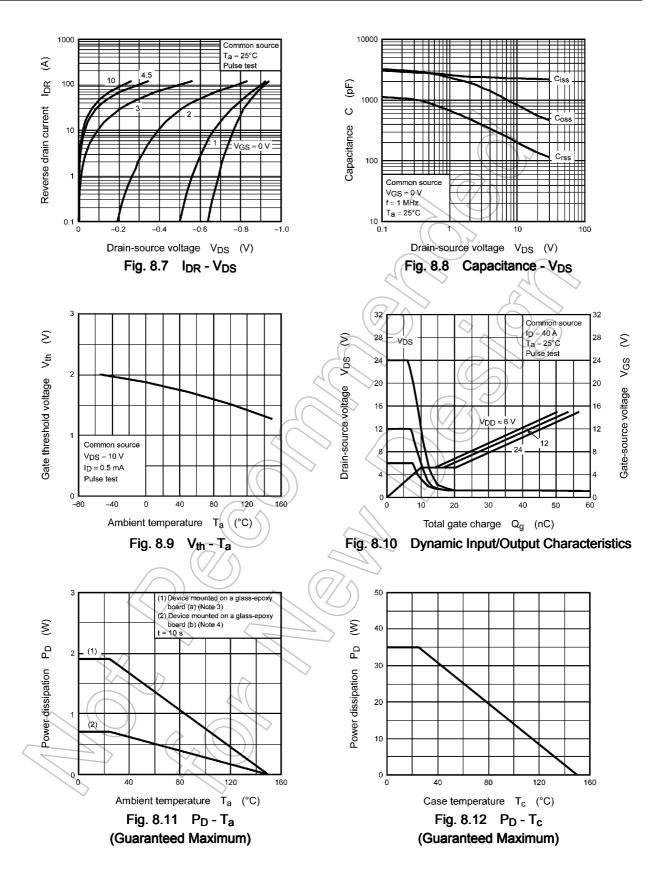
Note 7: Ensure that the channel temperature does not exceed 150°C.

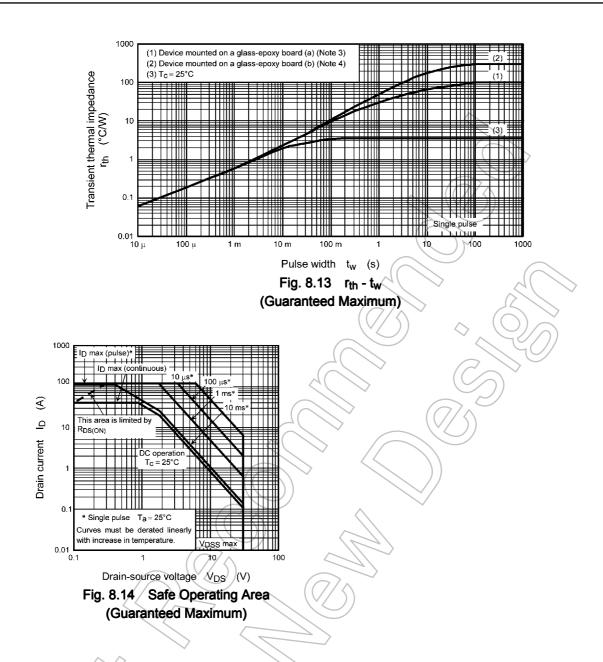
## 7. Marking



## 8. Characteristics Curves (Note)



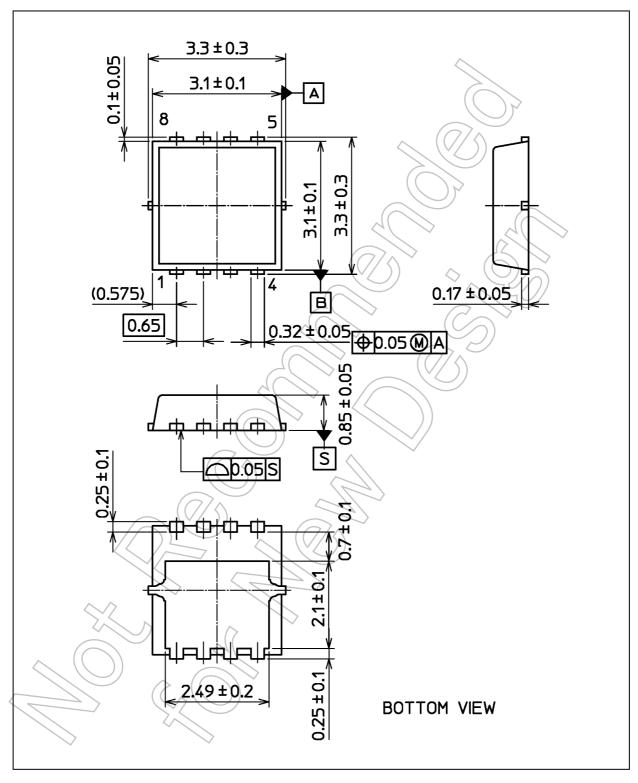




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TOSHIBA

Unit: mm



#### Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance

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